

650V Silicon Carbide Schottky Diode

GENERAL DESCRIPTION

- ◆ 650V Schottky rectifier
- ◆ Zero Forward/Reverse Recovery Current
- ◆ High Blocking Voltage
- ◆ High frequency operation
- ◆ Temperature Independent Switching Behavior
- ◆ Positive temperature coefficient of forward voltage(VF)

BENEFIT

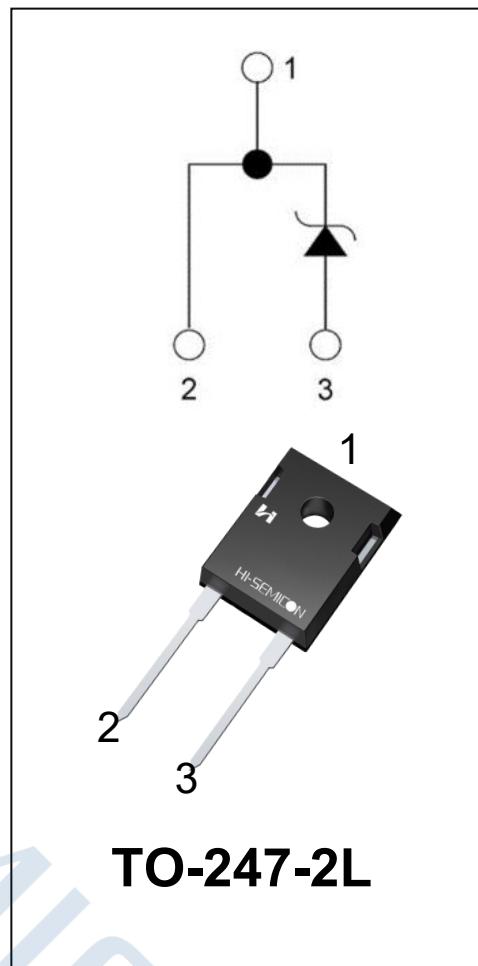
- ◆ Parallel Device Convenience without thermal runaway
- ◆ Higher Temperature Application
- ◆ Higher System Efficiency
- ◆ Hard Switching & Higher Reliability
- ◆ No Switching loss
- ◆ Environmental Protection

Product Summary

- ◆ $V_R=650V$
- ◆ $I_F=20A(TC=140^\circ C)$
- ◆ $Q_c=44nC(V_R=400V)$

Applications

- ◆ Uninterruptable power supplies
- ◆ AC/DC converters
- ◆ DC/DC Converters



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SC3D20065H	TO-247-2L	C3D20065	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS ($T_J=25^\circ\text{C}$ unless otherwise noted)

Characteristics		Symbol	Ratings	Unit
Repetitive peak reverse voltage		V_{RRM}	650	V
Continuous forward current	$T_C=25^\circ\text{C}$	I_F	55	A
	$T_C=135^\circ\text{C}$		24	
	$T_C=145^\circ\text{C}$		20	
Repetitive peak forward surge current	$tp=10\text{ms } T_C=25^\circ\text{C}$	I_{FRM}	110	A
	$tp=10\text{ms } T_C=110^\circ\text{C}$		100	
Non-repetitive peak forward surge current	$tp=10\text{ms } T_C=25^\circ\text{C}$	I_{FSM}	120	A
	$tp=10\text{ms } T_C=110^\circ\text{C}$		110	
Power dissipation	$T_C=25^\circ\text{C}$	P_{tot}	167	W
	$T_C=110^\circ\text{C}$		72	
Operating junction temperature		T_J	-55~175	°C
Storage temperature range		T_{stg}	-55~175	
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		TL	300	°C

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
DC Blocking Voltage	V_{DC}	$T_J=25^\circ\text{C}$	650	--	--	V
Forward voltage drop	V_F	$I_F=20\text{A}, T_J=25^\circ\text{C}$	--	1.5	1.8	V
		$I_F=20\text{A}, T_J=125^\circ\text{C}$	--	1.6	--	
		$I_F=20\text{A}, T_J=175^\circ\text{C}$	--	1.7	--	
Reverse leakage current	I_R	$V_R=650\text{V}, T_J=25^\circ\text{C}$	--	20	80	uA
		$V_R=650\text{V}, T_J=125^\circ\text{C}$	--	120	--	
		$V_R=650\text{V}, T_J=175^\circ\text{C}$	--	250	--	
Total capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$	--	770	--	pF
		$V_R=200\text{V}, f=1\text{MHz}$	--	90	--	
		$V_R=400\text{V}, f=1\text{MHz}$	--	64	--	
Total capacitance charge	Q_C	$V_R=400\text{V}, T_J=25^\circ\text{C}$	--	44	--	nC

THERMAL CHARACTERISTICS

Characteristics	Symbol	Typ.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.9	°C/W

Typical Performance Characteristics

Figure.1: Forward characteristics

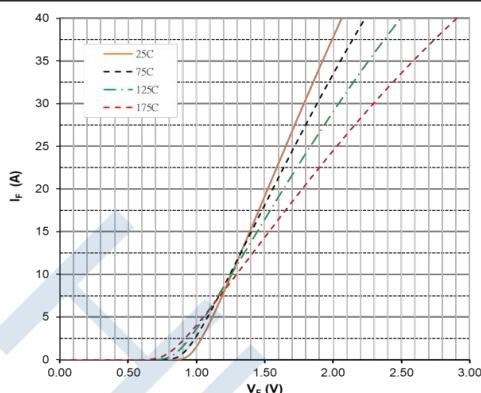


Figure.2: Forward Characteristics

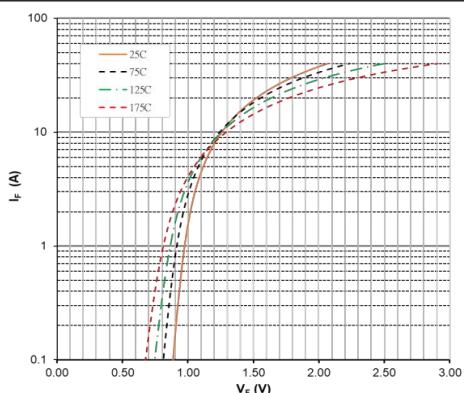


Figure.3: Reverse Characteristics

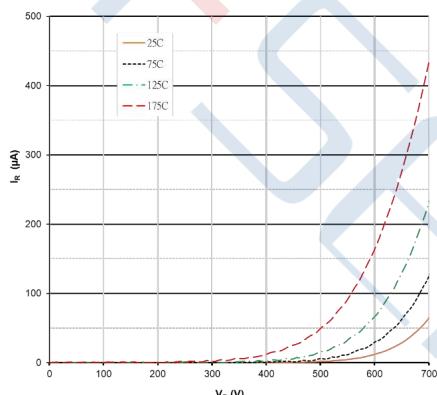


Figure.4: Power Derating

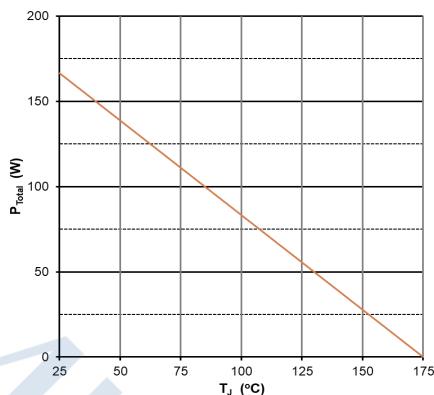


Figure.5: Reversecharge vs. Reverse Voltage

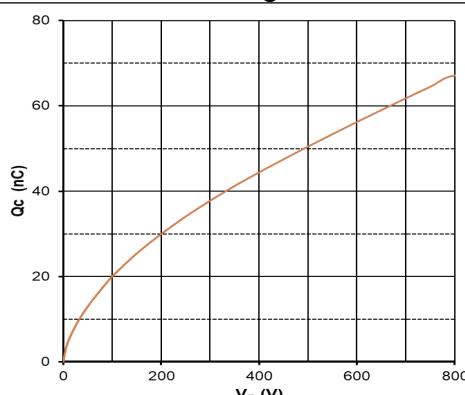
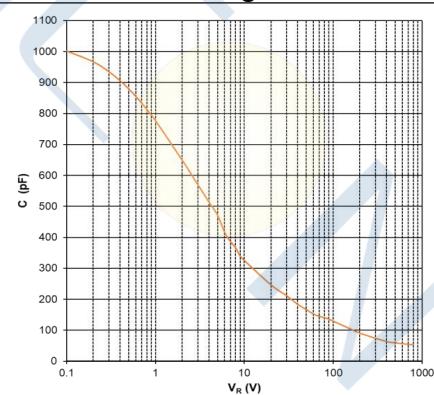
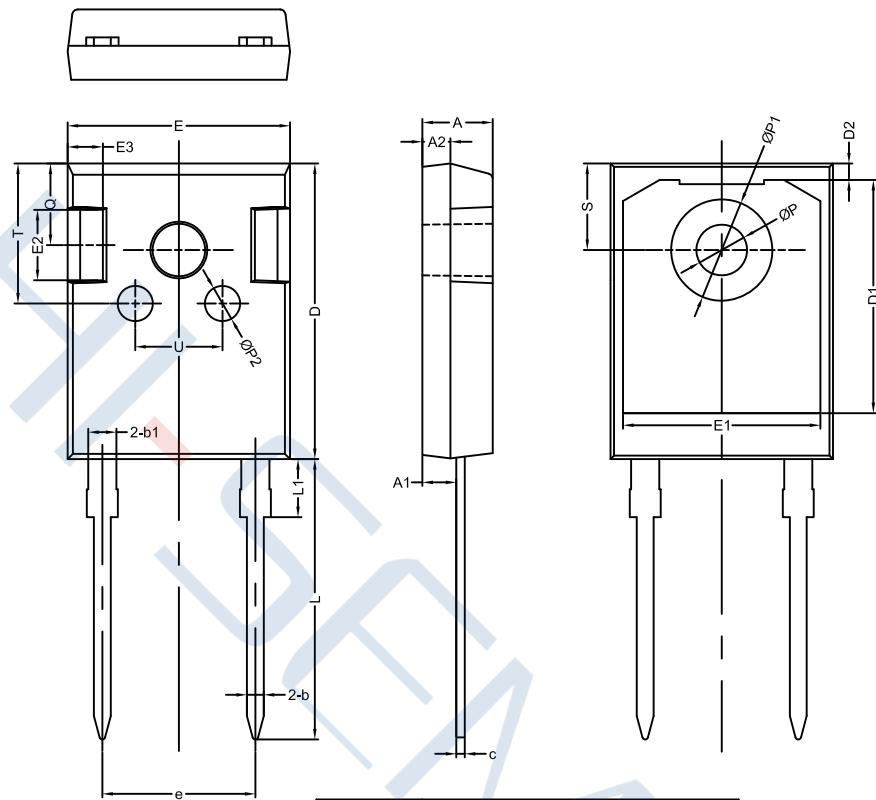


Figure.6: Capacitance vs. Reverse Voltage



Package Dimensions of TO-274-2L



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1		2.00	
c	0.55	0.60	0.75
D	20.80	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.0
E1		14.02	
E2		5.00	
E3		2.50	
e		10.88	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1		7.19	
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

Disclaimer:

- Hi-semicon reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- All semiconductor products malfunction or fail with some probability under special conditions. When using Hi-semicon products in system design or complete machine manufacturing, it is the responsibility of the buyer to comply with the safety standards strictly and take essential measures to avoid situations in which a malfunction or failure of such Hi-semicon products could cause loss of body injury or damage to property.
- Hi-semicon will supply the best possible product for customers!